

## **isc Silicon NPN Power Transistor**

# MJE3055

### DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  - :  $V_{(BR)CEO} = 60V(Min)$
- High DC Current Gain-
  - : h<sub>FE</sub>= 20-100@I<sub>C</sub>= 4A
- Complement to Type MJE2955
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

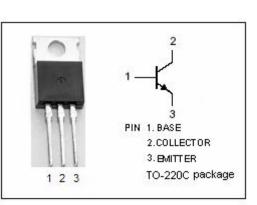
• Designed for use in general-purpose amplifier and switching applications.

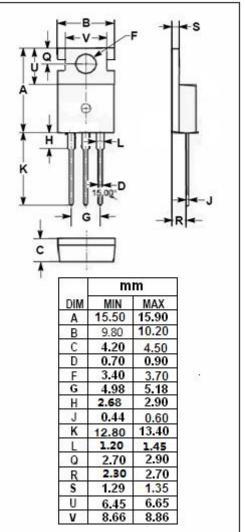
## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	70	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous	10	А	
I <sub>B</sub>	Base Current-Continuous	6	А	
Pc	Collector Power Dissipation @ Tamb=25℃	2	W	
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case		°C/W





isc Website: <u>www.iscsemi.com</u>



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# **ELECTRICAL CHARACTERISTICS**

 $T_c=25^{\circ}C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	60			v
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A			1.1	v
Vce(sat)-2	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 3.3A			8.0	v
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 4V			1.8	v
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> = 0			0.7	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 70V; I <sub>E</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 4V	20		100	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 4V	5			
f⊤	Current Gain-Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V; f= 500kHz	2.0			MHz

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